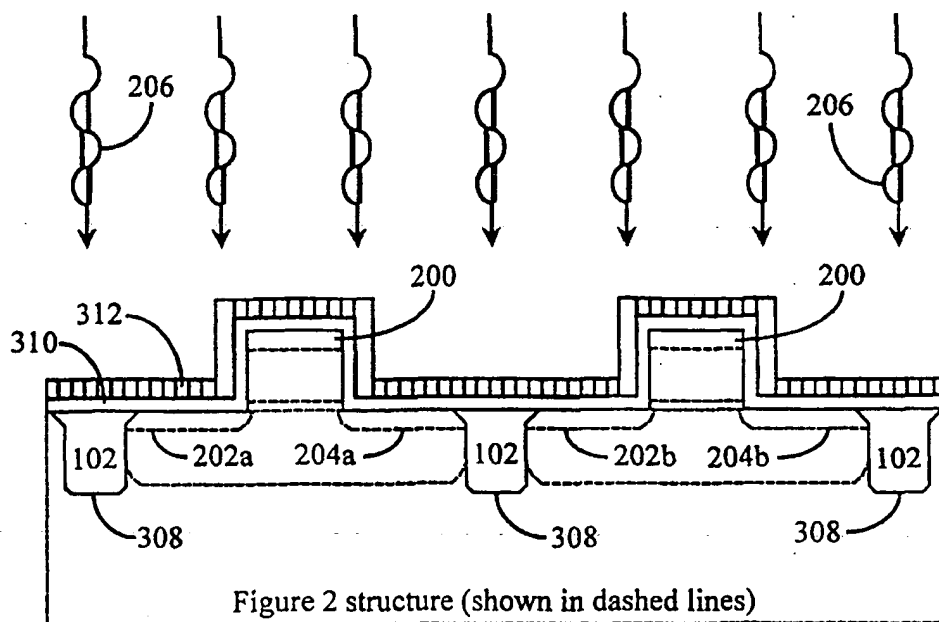




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(54) Title: GAS IMMERSION LASER ANNEALING METHOD SUITABLE FOR USE IN THE FABRICATION OF REDUCED-DIMENSION INTEGRATED CIRCUITS



## (57) Abstract

A method for fabricating a plurality of shallow-junction metal oxide semiconductor field effect transistors (MOSFETs) which are separated by substantially transparent isolation elements (102). This method includes the amorphization of a selected depth of silicon (200) in a silicon wafer. A top layer stack of a dielectric and a highly radiation absorbent material are deposited to protect areas of which amorphization is not desired. After the melted silicon has cooled and recrystallized, the top layer of highly absorbent material is removed.

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# GAS IMMERSION LASER ANNEALING METHOD SUITABLE FOR USE IN THE FABRICATION OF REDUCED-DIMENSION INTEGRATED CIRCUITS

## BACKGROUND OF THE INVENTION

### Field of the Invention:

This invention relates to the fabrication of integrated circuits (IC) and, more particularly, to the fabrication of IC comprising metal oxide semiconductor field-effect transistors (MOSFET) employing shallow junction formation.

### Description of the Prior Art:

Incorporated by reference herein is U.S. patent application 08/792,107, filed January 31, 1997 and assigned to the assignee of the present application. The present invention and the aforesaid patent application are concerned with alternative solutions to a problem which arises in the fabrication of MOSFETs (e. g., CMOS field-effect transistors), having gate length dimensions that are scaled down from 0.25  $\mu\text{m}$  to only 0.18  $\mu\text{m}$ . For the 0.18  $\mu\text{m}$  CMOS technology, these junction depths are projected, by the Semiconductor Industry Association's "The National Technical Roadmap for Semiconductors" (1995), to be less than 80 nm.

The first step of each of these alternative solutions is to amorphize a selected surface layer of crystalline silicon of each MOSFET to a selected depth. However, the remaining steps of each of these alternative solutions are different from one another.

In the case of the solution disclosed in the aforesaid patent application, a selected amount of doping material is deposited as a film on the surface of the amorphized selected surface layer of the silicon and then at least a portion of the amorphized selected surface layer of the silicon is temporarily heated, using prior-art projection gas immersion laser doping (P-GILD), for a certain time to a temperature which is sufficient to melt amorphized silicon but is insufficient to melt crystalline silicon (since the melting temperature of amorphized silicon is substantially below that of crystalline silicon). P-GILD is a relatively new technique, known in the art, for

doping silicon that eliminates up to 11 steps in the current process and can produce very shallow, sharply-defined regions of doping covering a wide range of doping concentrations. A revolutionary approach to impurity incorporation at precise locations in the silicon, P-GILD eliminates the need to build a mask on the wafer in order to define the regions to be doped prior to implantation. In accordance with the teaching of the aforesaid patent application, doping depth (and, hence, the depth of the junctions being formed in the selected surface layer) is determined solely by the depth of the melted amorphized selected surface layer. After the completion of the certain heating time, the melted silicon of the heated portion is permitted to cool, thereby effecting a recrystallization of the silicon of this portion of the selected surface layer. Finally, the recrystallized silicon of this portion of the selected surface layer may be annealed

As known, amorphization implants produce supersaturation of point defects. Upon annealing, point defect injection results in nucleation of extended defects. A critical annealing temperature applied for a selected time (e.g., 1050 °C for 10 sec.) by means of conventional rapid thermal processes is ordinarily required to anneal out the extended defects. However, the laser melting of the amorphized silicon by the P-GILD doping operation inherently provides a certain amount of annealing. Further, due to the small number of point defects present after the laser process, the junctions are not likely to move much as a result of this thermal cycle. Therefore, as speculated in the aforesaid patent application, no additional anneal for laser annealed junctions may be necessary. However, as further speculated in the aforesaid patent application, the exact extent of the diffusion after laser annealing needs to be determined experimentally in order to determine if any additional annealing is necessary.

The solution provided by the present invention employs prior-art ion implantation of dopants in at least a portion of the selected amorphized surface layer of the silicon and then the surface layer of the silicon is temporarily heated, using laser thermal annealing (LTA), for a certain time to a temperature which is sufficient to melt amorphized silicon but is insufficient to melt crystalline silicon (since the melting temperature of amorphized silicon is substantially below that of crystalline silicon). After the completion of the certain heating time, the melted silicon of the heated

portion is permitted to cool, thereby effecting a recrystallization of the silicon of this portion of the selected surface layer.

Although the LTA process is similar in certain respects to the P-GILD process, the LTA process is materially different in other respects from the P-GILD process. In both processes, a selected area of a silicon wafer is immersed in a gas and high-power projected laser radiation is used to heat the immersed gas and those particular regions of the wafer surface that are then being illuminated by the radiation. However, the immersion gas employed in the P-GILD process is an active gas which includes vaporized dopants, while the immersion gas employed in the LTA process is a relatively inert gas, such as nitrogen. Further, in the P-GILD process, the resolution capability of the projection optics must be high enough to accurately image a group of spaced reticle patterns on a corresponding group of sharply-defined spaced regions of doping of the silicon wafer. In the LTA process, however, the resolution capability of the projection optics (which need be only sufficient to flood the entire selected area of the silicon wafer with the illuminating radiation) is significantly lower than the high resolution capability of the projection optics needed by the P-GILD process. Therefore, it is plain that projection optics suitable for use with the LTA process is simpler and less costly than projection optics suitable for use with the P-GILD process. However, for the LTA process to be manufacturable in the fabrication of MOSFETs employing shallow junction formation, the process margins must be large enough to account for laser illumination energy fluctuations. This condition can be met with the correct choice of lasers and proper spatial homogenization of the laser illumination.

Nevertheless, problems arise in the fabrication of MOSFETs employing shallow junctions when the LTA process is applied directly to the silicon wafer surface at the point in the fabrication process that follows the implantation of dopants in the amorphized silicon layer. These problems are due to the fact that the silicon wafer surface is not a uniform absorber of the incident radiation. This non-uniformity results in geometry effects over the radiation-flooded selected area that cause fluctuations and shifts in the melt threshold of the shallow-junction MOSFETs being fabricated. Such melt threshold shifts introduce too much variability for the LTA process, as known, to be viable.

The present invention addresses this melt-threshold-shift shortcoming,

thereby making the LTA process manufacturable in the fabrication of a plurality of shallow-junction MOSFETs, which MOSFETs are spaced from one another by substantially transparent isolation elements.

#### Summary of the Invention

5 Disclosed is an improvement in a method for fabricating, on a selected area of a surface layer of a substrate, at least certain portions of source and drain junctions of a plurality of spaced MOSFETs. The selected area includes an isolation element composed of a first selected material that is substantially transparent to selected-wavelength laser radiation disposed between the crystalline silicon material of  
10 adjacent ones of the plurality of MOSFETs being fabricated. One step in the aforesaid method comprises amorphizing a surface layer of the crystalline silicon material of the plurality of MOSFETs being fabricated to a selected depth. The improvement in the aforesaid method further comprises the following steps:

1) —————> ion implanting a selected dosage of dopants of the appropriate type in  
15 the silicon surface layer of the plurality of n-channel or p-channel MOSFETs being fabricated either before or after the amorphizing step;

2) —————> depositing at least a layer of a second selected material of a first selected thickness over the entire selected area of the surface layer of the substrate, the layer of the second selected material (1) being absorbent of  
20 selected-wavelength laser radiation incident thereon (2) having a melting temperature higher than that of crystalline silicon, and (3) having a surface that is situated in an exposed position with respect to incident selected-wavelength laser; and

3) —————> then flooding the entire selected area of the surface of the layer of the second selected material with a selected value of substantially uniform energy  
25 laser radiation of the selected wavelength, the selected value being such as to result in the silicon underlying the selected area being heated to a temperature which is sufficient to melt amorphized silicon but insufficient to melt crystalline silicon.

30 Upon cooling, the melted silicon recrystallizes, thereby ensuring that the depth of the certain portions of the source and drain junctions of the plurality of spaced MOSFETs is determined solely by the selected depth of the amorphized surface

layer.

#### Brief Description Of The Drawings

FIGURE 1 (which is identical to FIGURE 1 of the aforesaid patent application) diagrammatically shows the structure of an n-channel and a p-channel FET that have been fabricated in accordance with modern silicon CMOS technology;

FIGURE 2 diagrammatically shows the structure of the two FIGURE 1 FETs that are to be fabricated in accordance with the method steps of the present invention at a fabrication stage which occurs just after (1) the fabrication of the FETs isolation elements, (2) the doping of the FETs wells, (3) the amorphization of the FETs silicon surface layers, and (4) the doping of the sources and drains of the FETs have been completed;

FIGURE 2a will be used to describe the melt-threshold-shift heating problem which would occur if the surface of the structure of FIGURE 2 were to be directly irradiated in accordance with the LTA process;

FIGURE 2b illustrates the variability of the reflectivity of  $\text{SiO}_2$  as a function of thickness compared to the constancy of the reflectivity of  $\text{SiO}_2$  as a function of thickness;

FIGURE 3 diagrammatically shows the structure of the two FIGURE 1 FETs that are to be fabricated in accordance with the method steps of the present invention at a later fabrication stage than that shown in FIGURE 2; and

FIGURE 3a will be used to describe the heating effect caused by the surface of the structure of FIGURE 3 being directly irradiated in accordance with the LTA process.

#### Description Of The Preferred Embodiment

Referring to FIGURE 1, there is shown 2 complimentary CMOS structures comprising silicon substrate 100, isolation elements 102 (composed of  $\text{SiO}_2$ ) and complimentary FETs 104a and 104b. The structure of complimentary FETs 104a and 104b differ only in that FET 104a comprises n well 106a,  $\text{p}^+$  source 108a and  $\text{p}^+$  drain 110a, while FET 104b comprises p well 106b,  $\text{n}^+$  source 108b and  $\text{n}^+$  drain 110b. In all other respects, the structure of complimentary MOSFETs 104a and 104b is similar. Specifically, both complimentary MOSFETs 104a and 104b comprise (1) gate poly 112 insulated from the well of that MOSFET by a thin layer 114 of  $\text{SiO}_2$ , (2) side

wall spacers 116 supporting the gate poly 112 of each of MOSFETs 104a and 104b, (3) silicide electrical contacts 117 situated on top of the respective gate poly, source and drain of each of complimentary MOSFETs 104a and 104b, and (4) lightly doped extensions 118 coupling the source and drain of each of complimentary MOSFETs 104a and 104b to the channel region under the gate poly.

It is apparent from FIGURE 1 that the shallowest junctions are the lightly doped extensions 118, which connect the deep sources and drains to the gate poly channel. Extensions 118 are needed to prevent drain induced barrier lowering (DIBL) and punchthrough.

The earliest steps of both the method disclosed in the aforesaid patent application and the method of the present invention for fabricating the complimentary MOSFETs 104a and 104b of FIGURE 1 involve the doping of silicon substrate 100 to form each of wells 106a and 106b, followed by the fabrication of gate poly 112 situated over a thin layer 114 of  $\text{SiO}_2$ . The next step, shown in FIGURE 2, of both the fabricating method disclosed in the aforesaid patent application and the method of the present invention comprises amorphizing, to the desired ultra-shallow depth of the extensions 118 being fabricated, those regions of the FIGURE 1 MOSFETs being fabricated which include the upper polycrystalline silicon layer 200 of gate poly 112 and the upper crystalline silicon surface layers 202a, 202b, 204a and 204b of well 106 (which surface layers 202a, 202b, 204a and 204b are to be included in the source and drains 108a, 108b, 110a and 110b of the MOSFETs being fabricated). Amorphization may be achieved by ion implantation of a heavy atom, such as argon, silicon or germanium. However, germanium is to be preferred because it is a heavy atom which requires low doses to amorphize silicon, produces abrupt amorphous-crystalline interfaces, and is isoelectronic in the silicon lattice.

More particularly, as shown in FIGURE 2, surface layers 202a, 202b, 204a and 204b on the side of gate poly 112, which are to be amorphized, extend all the way to an isolation element 102. Assuming, by way of example, that the desired ultra-shallow depth of these layers to be amorphized is substantially 30 nm (which is less than 80 nm), a dose of  $2 \times 10^{14}$  atoms/cm<sup>2</sup> is required to achieve this desired 30 nm amorphization depth. A 20 KeV germanium implant at a dose of  $2 \times 10^{14}$  atoms/cm<sup>2</sup> achieves this desired 30 nm amorphization depth of the layers 202 and 204. This



implant condition is easily obtainable using existing high current implanters. However depending on the desired amorphous depth, the range of implant dose is between  $1 \times 10^{13}$  atoms/cm<sup>2</sup> and  $1 \times 10^{16}$  atoms/cm<sup>2</sup>, while the range of implant energy is between 5 keV and 400 keV.

5 In the next step of the method of the present invention, amorphized layers 202a and 204a have a p<sup>+</sup> dose of dopant (e.g., boron) ion implanted therein and layers 202b and 204b have an n<sup>+</sup> dose of dopant (e.g., phosphorous or arsenic) ion implanted therein. A typical dosage for the lightly-dosed extensions is  $5 \times 10^{14}$  atoms/cm<sup>2</sup>. The implant energies for boron, phosphorous and arsenic typically are, 10 respectively, 250, 2000 and 5000 electron volts. More generally, ion-implant dosages can range between  $10^{13}$  to  $10^{16}$  atoms/cm<sup>2</sup> and the implant energies can range between 10 and 100,000 electron volts.

Referring now to FIGURE 2a, there is shown the melt-threshold-shift heating problem which would occur if the surface of the structure of FIGURE 2 were 15 to be directly irradiated in accordance with the LTA process. In FIGURE 2a, the FIGURE 2 structure is shown in dashed lines. The entire top surface of this structure is flooded by substantially uniform high-power laser radiation 206. Applicant has employed a pulsed XeCl excimer laser operating at a wavelength of 308 nm for deriving radiation 206, although another type of excimer laser (e.g., a 193 nm ArF 20 laser, a 248 nm KrF laser or a 351 nm XeF laser) could be used instead. While the fluence range for laser irradiation extends all the way from 0.05 Joules per cm<sup>2</sup> and 1.0 Joules per cm<sup>2</sup>, the most likely radiation fluence sufficient to heat amorphized silicon to its melting temperature, but insufficient to heat crystalline silicon to its melting temperature, is 0.6 Joules per cm<sup>2</sup>.

25 It should be noted that isolation elements 102 are composed of SiO<sub>2</sub> which is substantially transparent to incident 308 nm radiation. Depending on the oxide thickness, the normally incident light is selectively absorbed in the silicon underlying the oxide isolation element or is reflected by the isolation element. This is graphically illustrated in Figure 2b which shows the reflectivity of a silicon oxide layer 30 sitting on top of silicon as a function of the oxide layer thickness. Light which is not reflected is absorbed in the underlying silicon. Since the reflectivity of uncoated silicon to incident 308 nm radiation is a constant 0.6, an oxide layer of the wrong thickness

can almost double the absorption. In cases where the SiO<sub>2</sub> isolation elements 102 are of optimal thickness for absorption, the underlying silicon is highly heated by the high-power laser radiation 206 traveling therethrough and can be melted, resulting in undesirable changes to the isolation structure. The solid outline in FIGURE 2a comprises (1) thick outline component 208a representing the relatively large amount of heat energy absorbed in the top surface of the silicon normal to directly incident high-power laser radiation 206, (2) thick outline component 208b representing the relatively large amount of heat energy absorbed in those surfaces of the silicon which are in contact with the bottom of the SiO<sub>2</sub> isolation elements 102 in response to heat energy transferred thereto from the isolation elements of optimal thickness for absorption, and (3) thin outline component 208c representing the relatively negligible amount of heat energy absorbed in those surfaces of the silicon which are approximately parallel to the incident radiation.

Although the silicon gate height and length are held to tight tolerances, large variations in the thickness of SiO<sub>2</sub> isolation elements 102 are common and to be expected. Hence, the heating of the silicon surface which is in contact with the bottom of the SiO<sub>2</sub> isolation elements 102 cannot be controlled. Extra heat in the isolation region can cause undesirable diffusion of the dopants in the wells and reduce the heat energy required to melt the amorphized regions of the source/drain and the gate. The degree of threshold lowering is dependent on the proximity of the source/drain regions and the SiO<sub>2</sub> isolation elements 102, and the thickness of the oxide isolation elements which determines the amount of incident 308 nm radiation absorbed in the silicon in contact with the SiO<sub>2</sub> isolation elements 102. This gives rise to the aforesaid melt-threshold-shift heating problem, in which device geometry and processing conditions strongly affect the amount of heat energy required to create the desired melt depth at the surface of the structure of FIGURE 2.

Applicant's solution to the aforesaid melt-threshold-shift heating problem is to make the surface absorption of radiation uniform by covering the entire top surface of the structure shown in FIGURE 2 with a deposited opaque layer of a material, such as most metals, metal oxides, metal nitrides, metal carbides, carbon, which is highly absorbent of all 308 nm radiation incident thereon and has a melting temperature which is higher than that of silicon. In the preferred embodiment of the

present invention shown in FIGURE 3, the opaque layer of material chosen comprises tantalum nitride because of its low reflectivity, high absorption and compatibility with silicon processing. Other desirable materials for the opaque layer are tungsten and tantalum. More specifically, in the preferred embodiment shown in FIGURE 3, the top surface of  $\text{SiO}_2$  isolation elements 102 and the top surface of amorphized silicon 200, 202a, 202b, 204a 204b are first covered with a relatively thin layer 310 (15 nm) of  $\text{SiO}_2$  and then this thin layer of  $\text{SiO}_2$  is covered with a relatively thick layer 312 (30 nm) of tantalum nitride. More generally, the thickness of the layer of  $\text{SiO}_2$  may range between 5 nm and 50 nm and the thickness of the layer of tantalum nitride is preferably sufficient to absorb all 308 nm radiation incident thereon and may range between 20 nm and 150 nm. In general, the thickness of a deposited opaque layer of material should be at least sufficient to result in this material absorbing greater than 50% of all of the of selected-wavelength laser radiation incident thereon. In any event, the need for the layer of  $\text{SiO}_2$  situated between the amorphized silicon and the layer of tantalum nitride arises to prevent the contamination of the silicon which would result if tantalum nitride were in direct contact with the silicon surface.

As is known, amorphous silicon has a factor of 10 lower thermal conductivity, a 300 °C lower melt temperature, and a 30 percent lower reflectivity than crystalline silicon. Referring to FIGURE 3a, high-power laser radiation 206 incident on the top surface of the highly absorbent tantalum nitride layer 312 is sufficient to heat layer 312 to a relatively high temperature. The heat when conducted through the thin  $\text{SiO}_2$  layer 310 to the top surface of the amorphized silicon 200, 202a, 202b, 204a 204b, is sufficient to melt the amorphized silicon 200, 202a, 202b, 204a 204b, but is insufficient to melt the crystalline silicon underlying the amorphized silicon, under the areas 202a, 202b, 204a and 204b in FIGURE 3a.

$\text{SiO}_2$  is a relatively poor conductor of heat and does not absorb the incident radiation directly. Therefore, as indicated in FIGURE 3a by thin solid line 308, the silicon in contact with the sides of isolation elements 102 is only negligibly heated as a result of the high-power laser radiation 206 incident on the top surface of tantalum nitride layer 312.

After the melted amorphized silicon layer is permitted to cool, thereby effecting a recrystallization of this layer, the tantalum nitride layer 312 is stripped.

The so-far described steps of the fabrication method of the present invention, which comprise the LTA process shown in FIGURES 3 and 3a, are employed for forming the ultra-shallow (preferably 30 nm depth) junctions of extensions 118. However, similar steps may be then used to fabricate the deep source and drain regions of the CMOS FET shown in FIGURE 1. Specifically, following the fabrication of the ultra-shallow junctions of extensions 118, side wall spacers 116 are fabricated. Thereafter, each of the deep source and drain regions located between each side wall spacer 116 and an isolation element 102 is reamorphized to its desired depth deeper than the above-described original amorphization thereof. This may be accomplished with higher energy (e.g., 40 KeV) and higher dose (e.g.,  $6 \times 10^{14}$  atoms/cm<sup>2</sup>) germanium implants. Following such reamorphization, additional dosage of dopants are added to the deep source and drain by ion implantation to preferably provide a total dosage of  $1 \times 10^{15}$  atoms/cm<sup>2</sup>. The implant energies for boron, phosphorous and arsenic remain, respectively, at 250, 2000 and 5000 electron volts, since the final fabricated deep source and deep junction depths are controlled solely by their amorphization depths. The amorphization step can be performed before or after the dopant implant step. The final steps for fabricating the deep source and deep junction comprise again employing the LTA process, which includes both depositing a tantalum nitride layer that has its top surface exposed to 308 nm radiation that is effective in melting only the amorphized silicon and thereafter stripping the tantalum nitride layer, to thereby form the source and drain junctions to a desired depth determined solely by the depth of the melted silicon of the fabricated CMOS FET. While the desired depth is preferably 120 nm, the range of desired depths is between 80 nm and 200 nm.

In the method of the preferred embodiment of the present invention described above, the fabrication of the deep source and drain involve the amorphization of the already-fabricated ultra-shallow (i.e., less than 150 nm depth) junctions, since these already-fabricated ultra-shallow junctions extend all the way to side wall spacers 116. However, it should be understood that the extent of the ultra-shallow junctions may be limited to solely the locations of the extensions and, therefore, not include the locations of the deep source and drain. In this case, the amorphization for the source and drain locations is independent of the amorphization

for the extension locations, so that the amorphization for the source and drain locations may occur either before or after the amorphization for the extension locations. Furthermore, the present invention may be employed for fabricating only the extensions of an MOSFET or, alternatively, only the deep source and drain of an MOSFET, rather than both of these.

Generalizing, depositing an absorbing layer on the silicon wafer surface ensures equal absorption of laser radiation across the entire wafer surface. This eliminates the unpredictability which would occur if absorption of laser radiation in isolation elements were to take place. Further, the heat source is moved to the wafer surface and, hence, no thermal trapping due to heat absorption in the silicon adjacent the isolation elements occurs. Therefore, the present invention makes the LTA process practical in the fabrication on a selected area of a silicon wafer of a plurality of isolated, spaced, very-shallow-junction MOSFETs.

## WHAT IS CLAIMED IS:

1. In a method for fabricating at least certain portions of source and drain junctions of each of a plurality of spaced MOSFETs on a selected area of a surface layer of a substrate, each one of said spaced MOSFETs including its own  
5 individually selected one of n and p channels, wherein said selected area includes an isolation element composed of a first selected material that is substantially transparent to selected-wavelength laser radiation disposed between crystalline silicon material of adjacent ones of said plurality of MOSFETs being fabricated, and wherein said method comprises the steps of:
  - 10 (a) amorphizing a surface layer to a selected depth of said crystalline silicon material of said plurality of MOSFETs being fabricated;
  - (b) selectively ion implanting, in the amorphized silicon surface layer corresponding to each individual MOSFET of said of said plurality of spaced MOSFETs being fabricated, a selected dosage of dopants of the appropriate n or p  
15 species for that individual MOSFET;
  - (c) depositing at least a layer of a second selected material of a first selected thickness over the entire selected area of said surface layer of said substrate, said layer of said second selected material (1) being absorbent of selected-wavelength laser radiation incident thereon (2) having a melting temperature higher than that of  
20 crystalline silicon; and
  - (d) then flooding the entire selected area of said surface of said layer of said second selected material with a selected value of substantially uniform energy laser radiation of said selected wavelength, said selected value being such as to result in the silicon underlying said selected area being heated to a temperature which is sufficient  
25 to melt amorphized silicon but insufficient to melt crystalline silicon;  
whereby, after said melted silicon has cooled, it recrystallizes.
2. The method defined in Claim 1, wherein step (c) comprises the step of:
  - (d) depositing a layer of a third selected material of a second selected  
30 thickness prior to the depositing of said second selected material, said third selected material exhibiting characteristics that prevent the amorphized silicon surface layer from being contaminated by direct contact with said second selected material.

3. The method defined in Claim 2, wherein:  
each of said first and third selected materials comprises  $\text{SiO}_2$  and said  
second selected material comprises tantalum nitride.
4. The method defined in Claim 3, wherein:  
said selected wavelength of said laser radiation is 308 nm.
5. The method defined in Claim 4, wherein:  
said first thickness of said titanium nitride second selected material is in  
the range of 20 nm to 150 nm and said third thickness of said  $\text{SiO}_2$  third selected  
material is in the range of 5 nm to 50 nm.
6. The method defined in Claim 5, wherein:  
said first thickness is substantially 30 nm and said third thickness is  
substantially 15 nm.
7. The method defined in Claim 2, wherein:  
each of said first and third selected materials comprises  $\text{SiO}_2$  and said  
second selected material comprises a selected one of a metal, metal oxide, metal  
nitride, metal carbide, carbon, tungsten, or tantalum.
8. The method defined in Claim 1, wherein:  
said first selected thickness is sufficient to result in said second selected  
material absorbing greater than 50% of all of said of selected-wavelength laser  
radiation incident thereon.
9. The method defined in Claim 1, wherein:  
each of said MOSFETs includes a gate portion; and  
said certain portions of said source and drain junctions of a MOSFET  
comprise less than 150 nm depth extension portions of said source and drain junctions  
that are spatially located in contiguous relationship with the gate portion of that  
MOSFET.
10. The method defined in Claim 10, wherein:  
said certain portions of said source and drain junctions of a MOSFET  
further comprise remaining portions having a depth in the range of 80 nm to 200  
nm.
11. The method defined in Claim 11, wherein:

said remaining portions of said source and drain junctions have a 15 depth of substantially 120 nm.

12. The method defined in Claim 1, wherein:

5 said certain portions of said source and drain junctions of a MOSFET comprise particular portions of said source and drain junctions having a depth in the range of 80 nm to 200 nm.

13. The method defined in Claim 13, wherein:

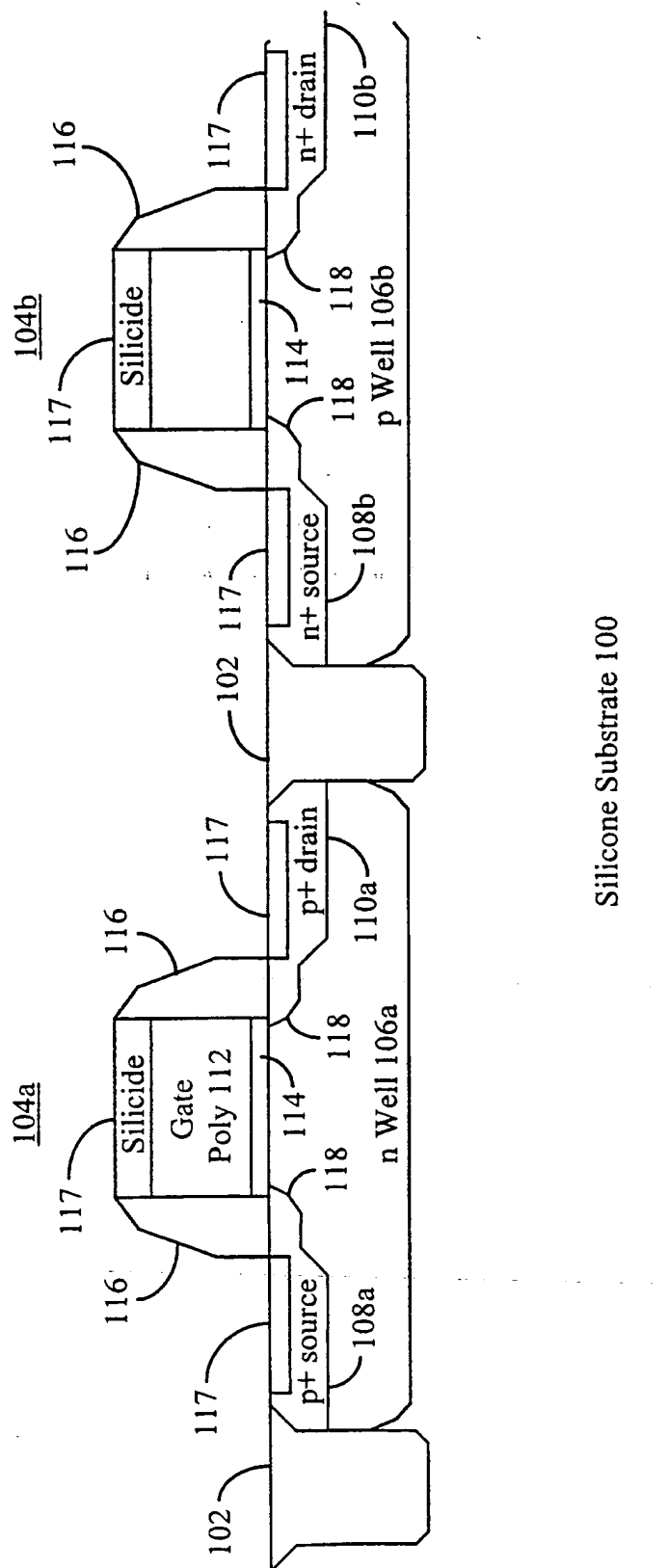
said particular portions of said source and drain junctions have a depth of substantially 120 nm.

10 14. The method defined in Claim 3, wherein said method comprises the further step of:

(e) after said melted silicon has recrystallized, stripping said deposited layer of said second selected material.

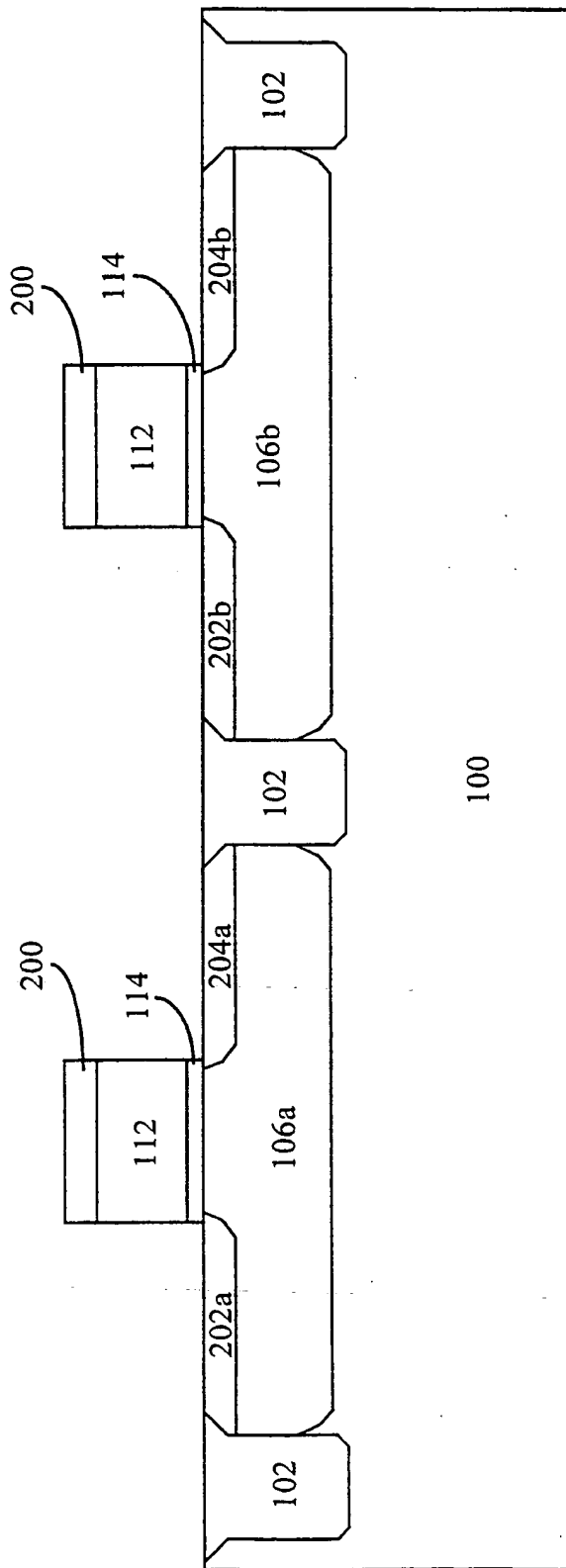
15 15. The method defined in Claim 1 wherein adjacent ones of said plurality of MOSFETs being fabricated comprise a pair of CMOS field-effect transistors.



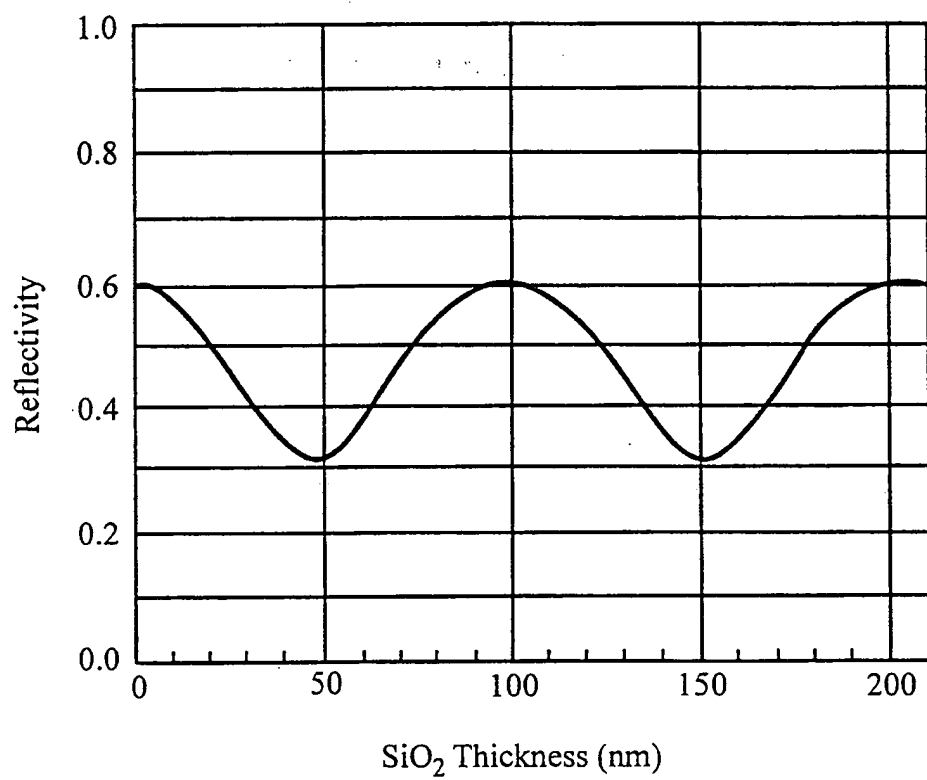


Silicone Substrate 100

*Fig. 1*



*Fig. 2*

*Fig. 2b*

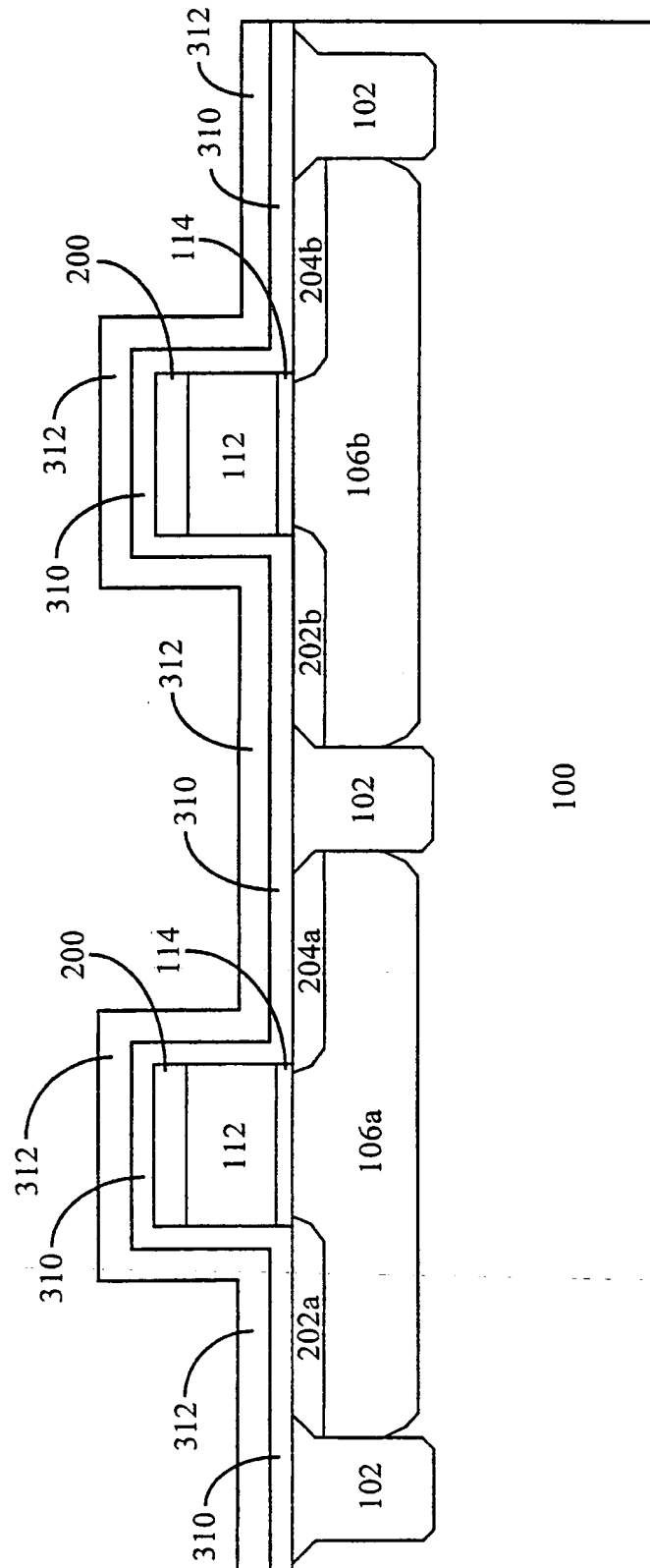
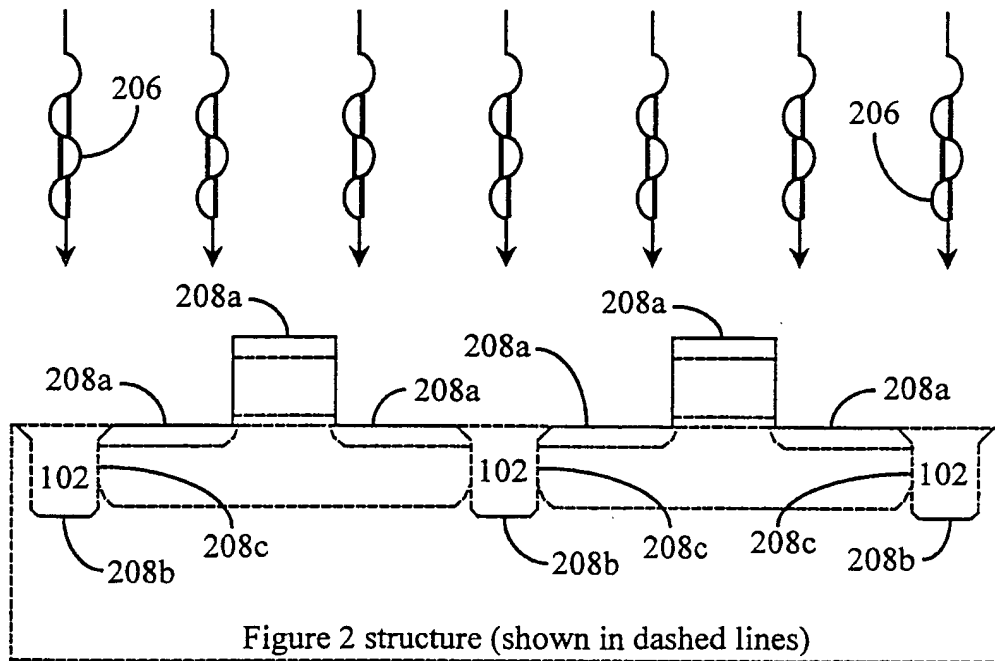
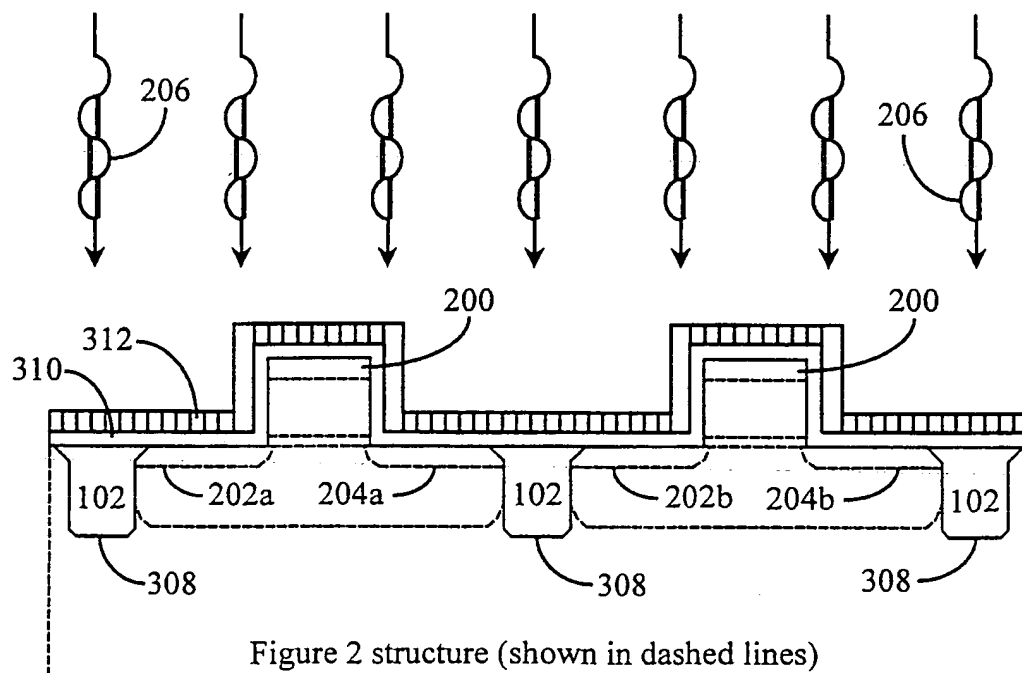


Fig. 3



**Fig. 2a**



**Fig. 3a**

## INTERNATIONAL SEARCH REPORT

International application No.

PCT/US98/25264

**A. CLASSIFICATION OF SUBJECT MATTER**

IPC(6) :H01L 21/20

US CL :438/482

According to International Patent Classification (IPC) or to both national classification and IPC

**B. FIELDS SEARCHED**

Minimum documentation searched (classification system followed by classification symbols)

U.S. : 438/482, 166, 474, 486, 487, 517, 520, 592

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

**C. DOCUMENTS CONSIDERED TO BE RELEVANT**

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
A	US 5,318,915 A (BALIGA ET AL.) 07 June 1994 (07.06.94), see abstract, column. 4 line 25.	1
A	US 5,087,576 A (EDMON ET AL.) 11 February 1992 (11.02.92), see col. 9 lines 24-56.	1,8-15
A	US 4,753,895 A (MAYER ET AL.) 28 June 1988 (28.06.98), see cloumns 4-8.	1, 8-15
A	US 4,371,421 A (FAN ET AL.) 01 February 1983 (01.02.83), see Fig. 1, col. 4 line 46-col. 6 line 59.	1, 8-15
A	US 5,077,233 A (MUKAI) 31 December 1991 (31.12.91), see column 1-10 lines 1-55.	1-15
A	US 4,659,392 A (VASUDEV) 21 April 1987 (21.04.87), see columns 2-4.	1

☒ Further documents are listed in the continuation of Box C.
 ☐ See patent family annex.

* Special categories of cited documents:	"T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention
"A" document defining the general state of the art which is not considered to be of particular relevance	"X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone
"E" earlier document published on or after the international filing date	"Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art
"L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)	"&" document member of the same patent family
"O" document referring to an oral disclosure, use, exhibition or other means	
"P" document published prior to the international filing date but later than the priority date claimed	

Date of the actual completion of the international search

15 JUNE 1999

Date of mailing of the international search report

03 AUG 1999

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## INTERNATIONAL SEARCH REPORT

International application No.  
PCT/US98/25264

C (Continuation). DOCUMENTS CONSIDERED TO BE RELEVANT		
Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
A	US 4,463,492 A (MAEGUCHI) 07 August 1984 (07.08.84), see columns 3-5.	1